

isc N-Channel MOSFET Transistor

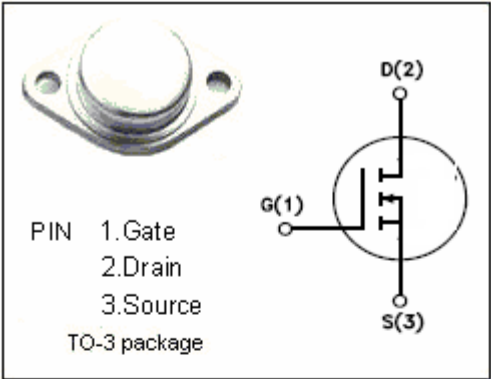
2N6770

DESCRIPTION

- VGS Rated at ±20V
- Silicon Gate for fast switching speeds
- IDSS 、 RDS(ON) ,specified at elevated temperature
- Low drive requirements

APPLICATIONS

designed for high voltage ,high speed application ,such as off-line switching power applies,UPS,AC and DC motor controls , relay and solenoid drivers.

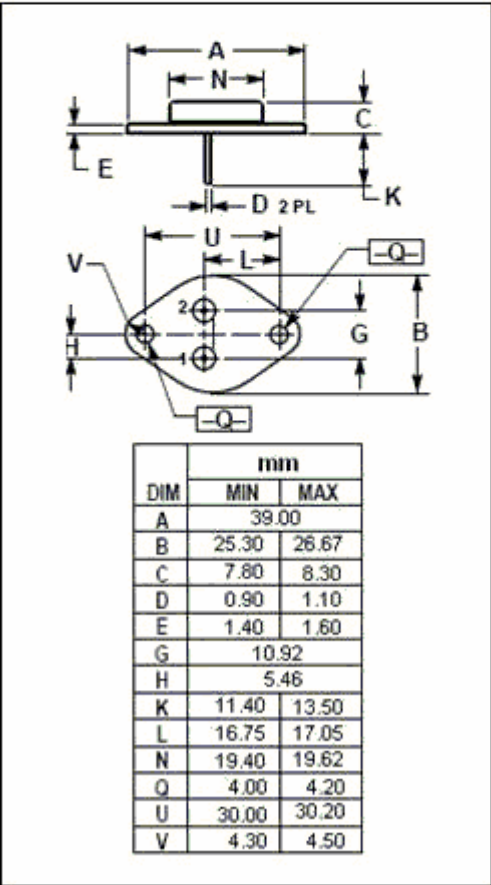


ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	500	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37°C	12	A
P _{tot}	Total Dissipation@TC=25°C	150	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	0.83	°C/W



isc N-Channel Mosfet Transistor**2N6770****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	500		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 7.75A		0.4	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = 20V; V _{DS} = 0		100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V; V _{GS} = 0		1	mA
V _{SD}	Diode Forward Voltage	I _F = 12A; V _{GS} = 0		1.6	V